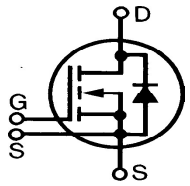
IXYS

GigaMOS™ TrenchT2 HiperFET™ Power MOSFET

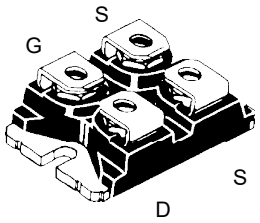
IXFN360N15T2

V_{DSS} = 150V
I_{D25} = 310A
$R_{DS(on)}$ ≤ 4.0mΩ
t_{rr} ≤ 150ns

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



miniBLOC, SOT-227
E153432



G = Gate D = Drain
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C		150	V
V_{DGR}	T_J = 25°C to 175°C, R_{GS} = 1MΩ		150	V
V_{GSS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C (Chip Capability)		310	A
$I_{L(RMS)}$	External Lead Current Limit		200	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}		900	A
I_A	T_C = 25°C		100	A
E_{AS}	T_C = 25°C		2.5	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 175°C$		20	V/ns
P_D	T_C = 25°C		1070	W
T_J			-55 ... +175	°C
T_{JM}			175	°C
T_{stg}			-55 ... +175	°C
V_{ISOL}	50/60 Hz, RMS	t = 1 minute	2500	V~
	$I_{ISOL} \le$ 1mA	t = 1 second	3000	V~
M_d	Mounting Torque		1.5/13	Nm/lb.in.
	Terminal Connection Torque		1.3/11.5	Nm/lb.in.
Weight			30	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	150			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA	2.5		5.0	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			50	μA
	T_J = 150°C			5	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 60A, Note 1			4.0	mΩ

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Synchronous Recification
- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 60A, Note 1	140	230		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		47.5		nF
C_{oss}			3060		pF
C_{rss}			665		pF
R_{Gi}	Gate Input Resistance		2.7		Ω
$t_{d(on)}$	**Resistive Switching Times** V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 100A R_G = 1Ω (External)		50		ns
t_r			170		ns
$t_{d(off)}$			115		ns
t_f			265		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 180A		715		nC
Q_{gs}			185		nC
Q_{gd}			200		nC
R_{thJC}				0.14	°C/W
R_{thCS}			0.05		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			360	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			1440	A
V_{SD}	I_F = 60A, V_{GS} = 0V, Note 1			1.2	V
t_{rr}	I_F = 160A, V_{GS} = 0V -di/dt = 100A/μs V_R = 60V			150	ns
Q_{RM}			500		nC
I_{RM}			9		A

Note 1. Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

Fig. 1. Output Characteristics @ T_J = 25ºC

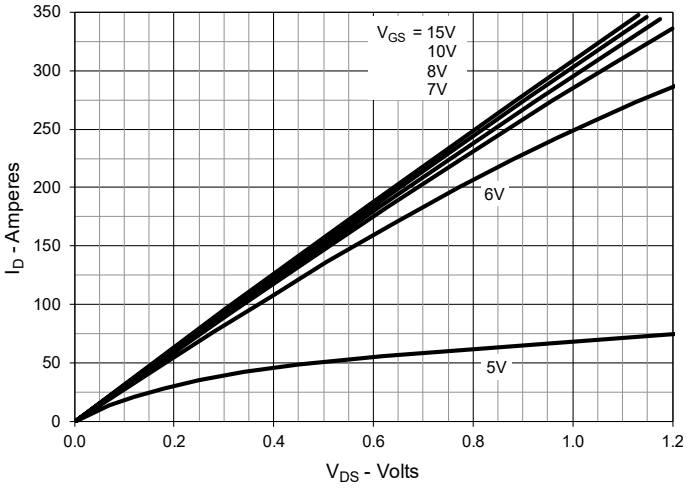


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

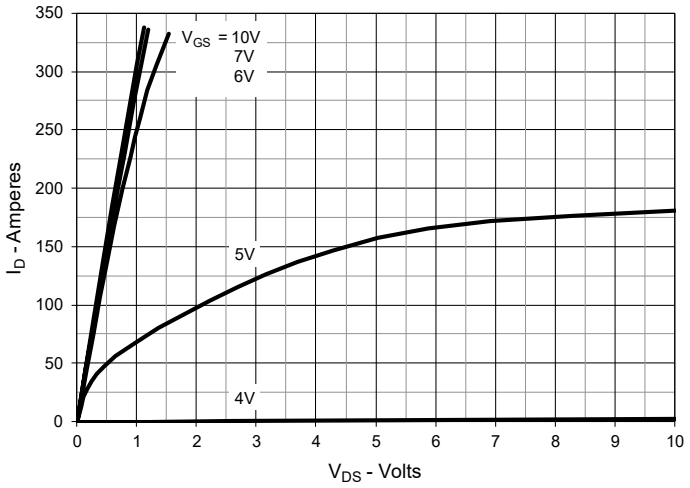


Fig. 3. Output Characteristics @ T_J = 150ºC

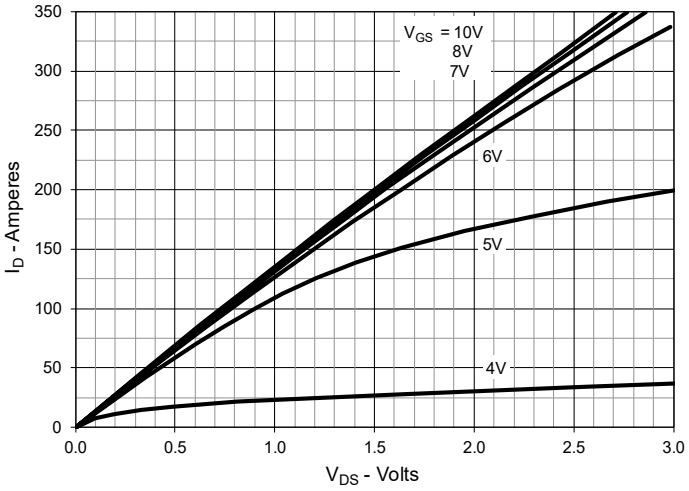


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 180A Value vs. Junction Temperature

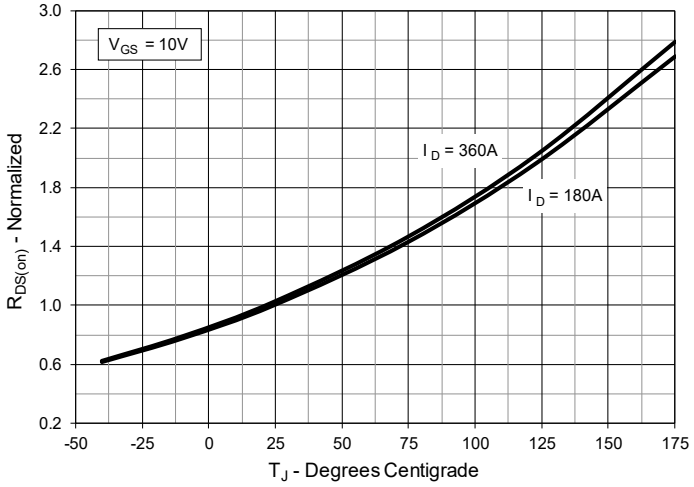


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 180A Value vs. Drain Current

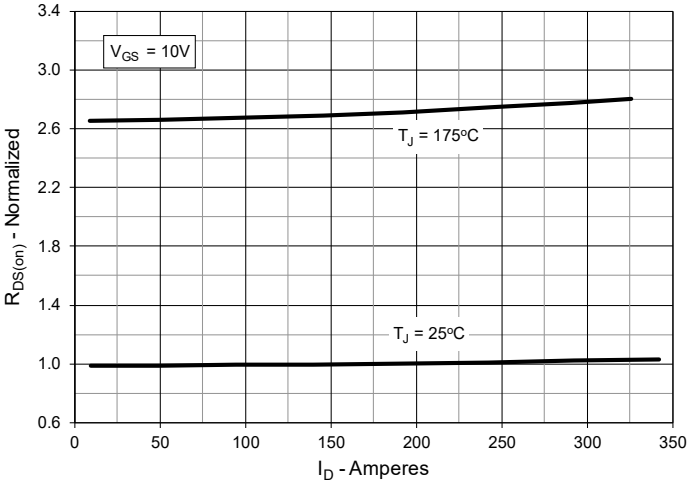


Fig. 6. Drain Current vs. Case Temperature

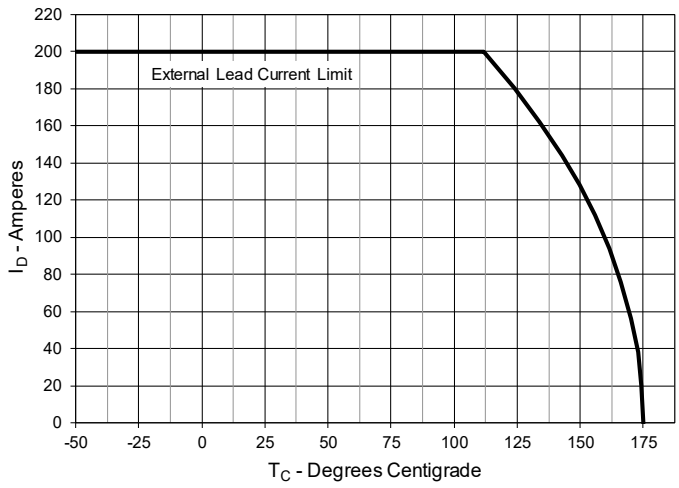


Fig. 7. Input Admittance

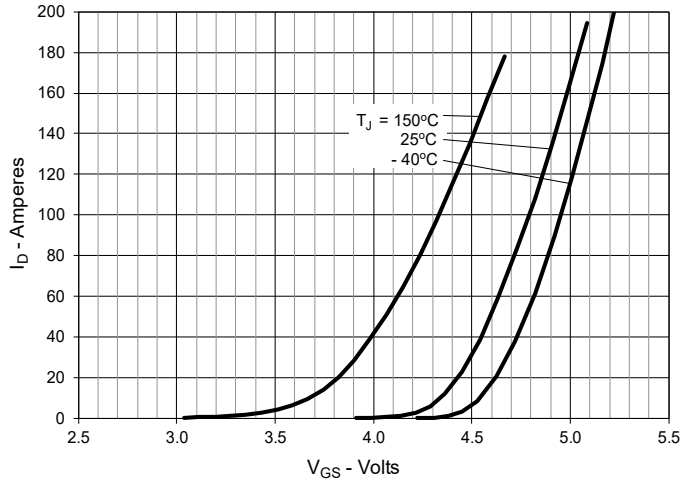


Fig. 8. Transconductance

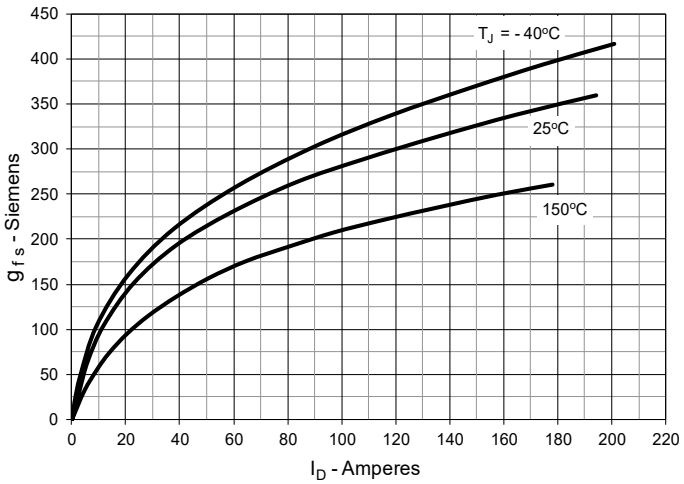


Fig. 9. Forward Voltage Drop of Intrinsic Diode

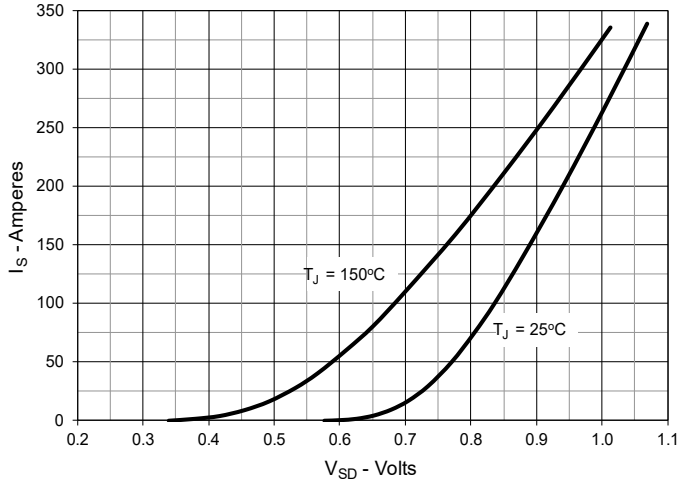


Fig. 10. Gate Charge

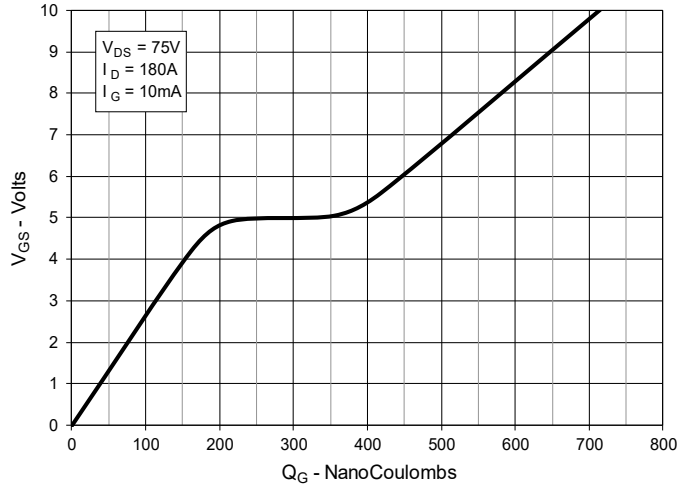


Fig. 11. Capacitance

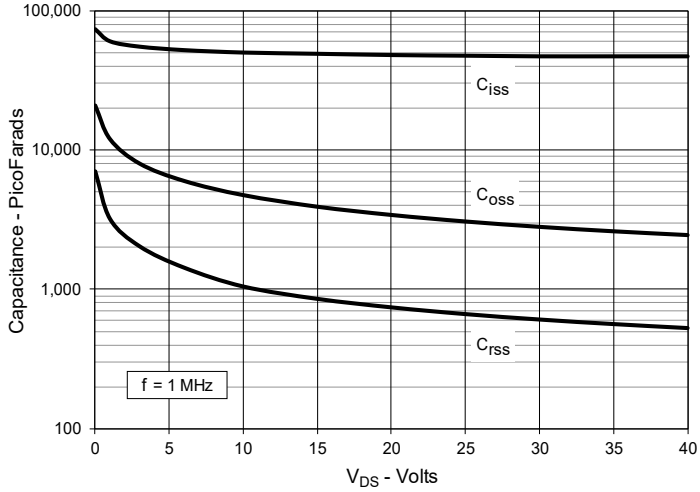


Fig. 12. Forward-Bias Safe Operating Area

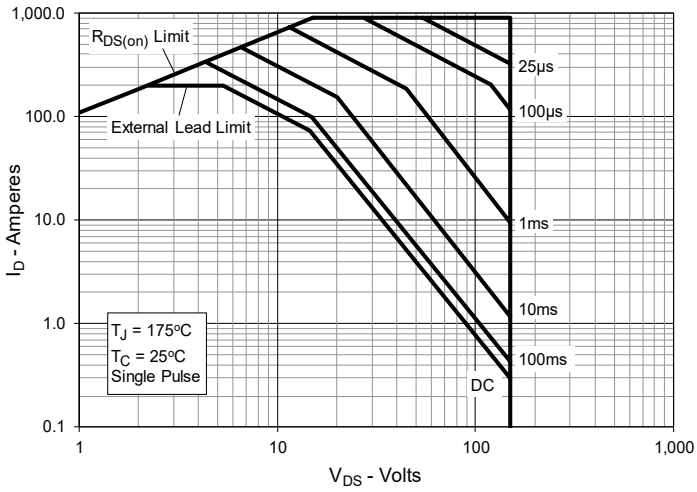


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

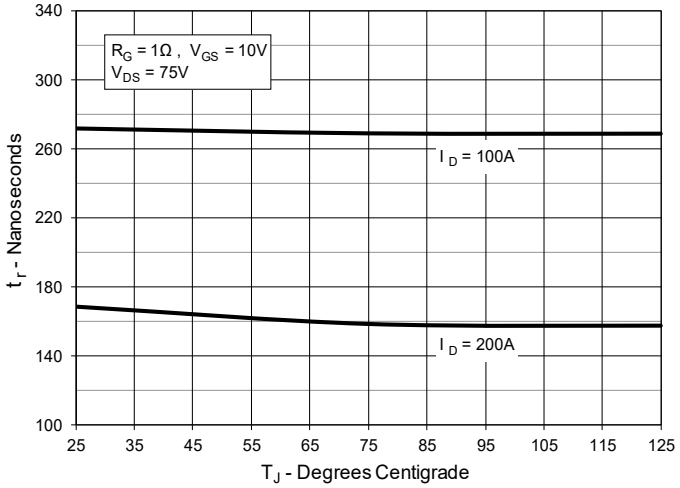


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

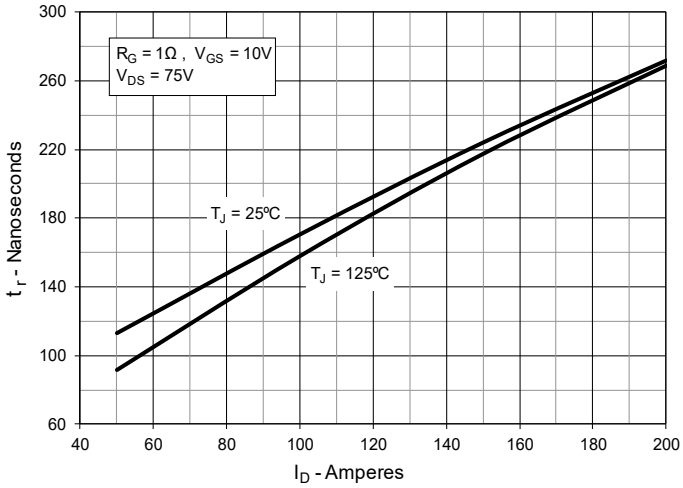


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

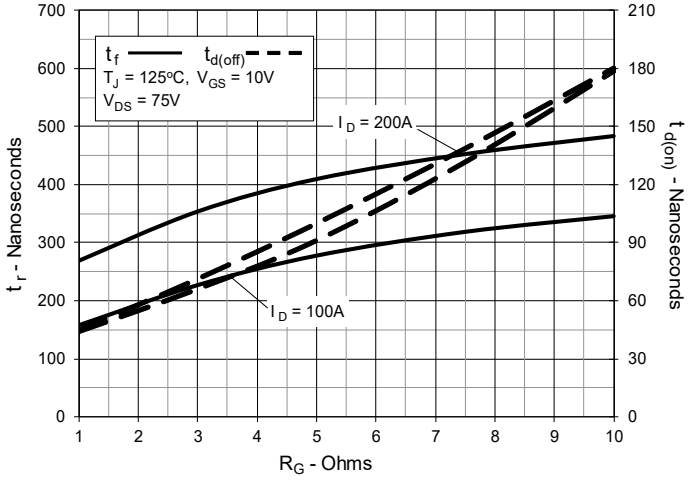


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

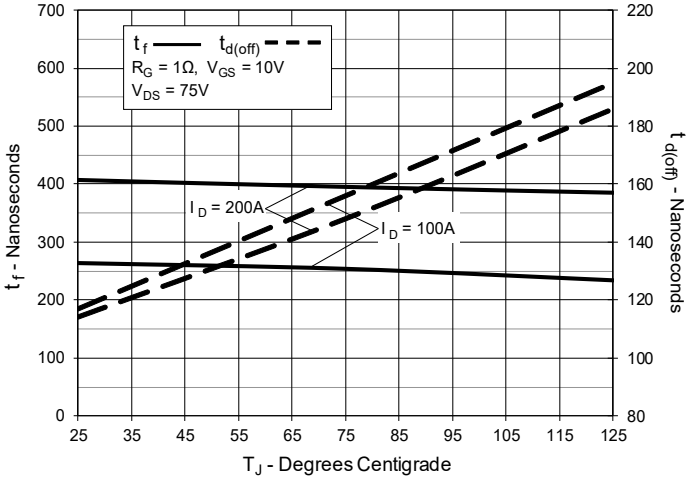


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

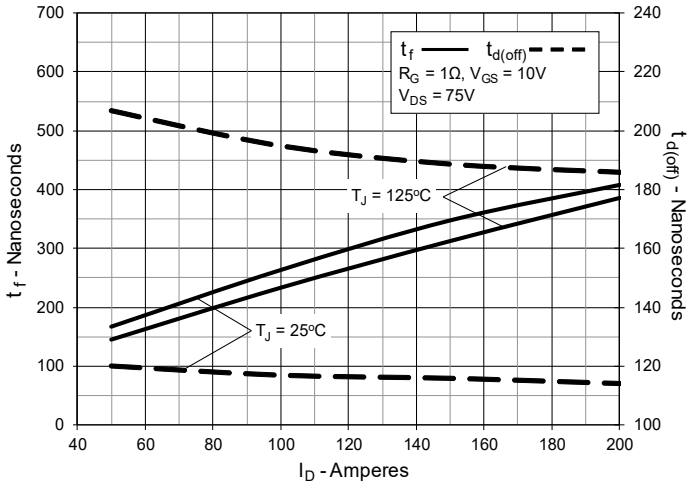


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

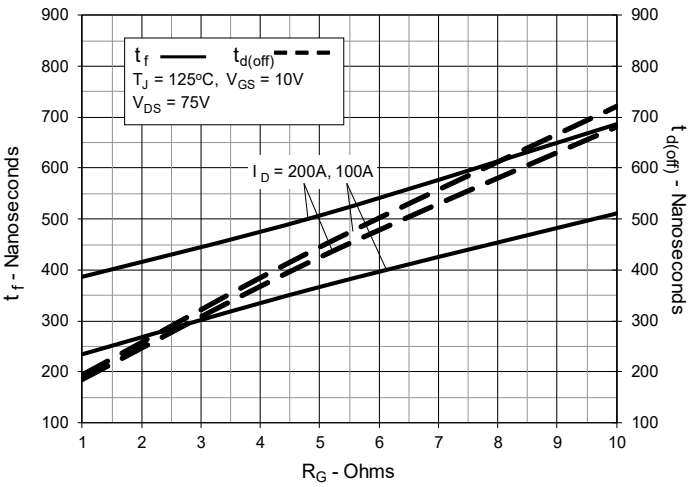
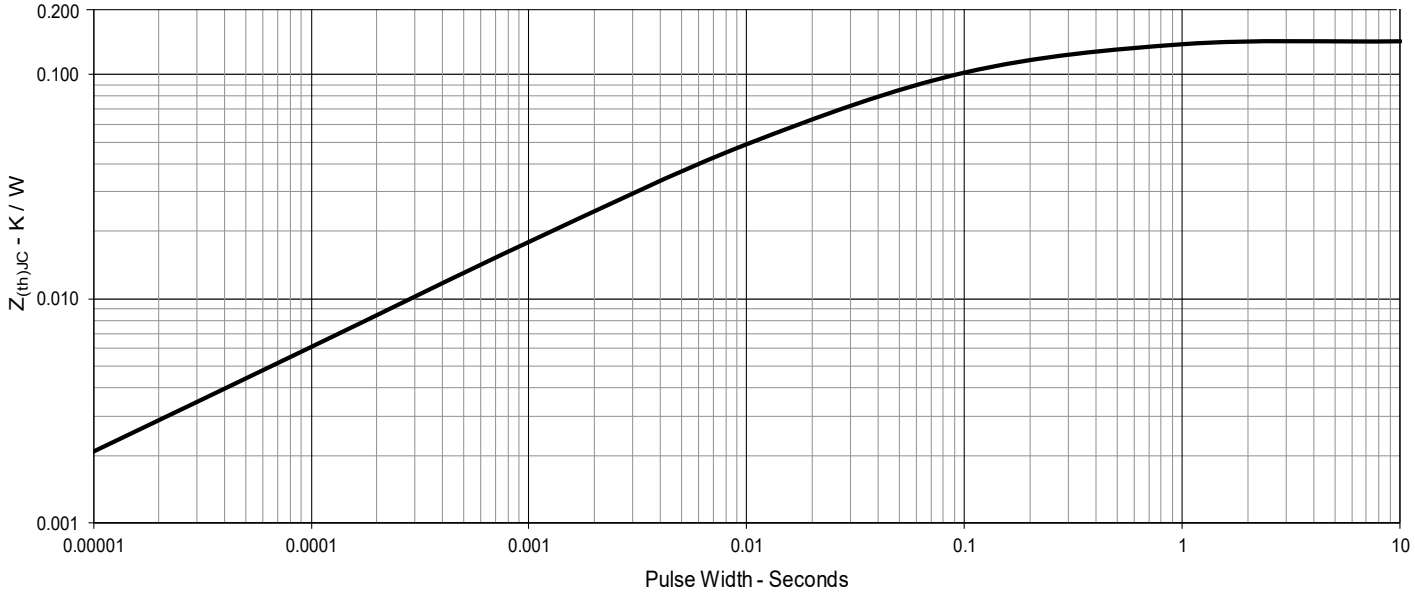
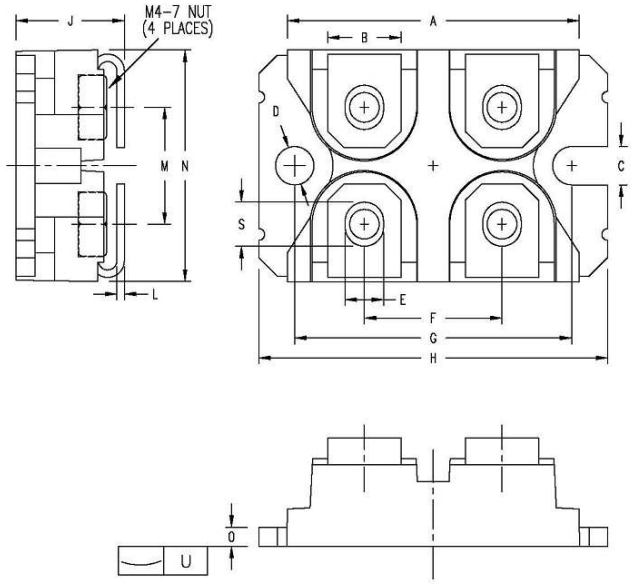


Fig. 19. Maximium Transient Thermal Impedance



SOT-227 miniBLOC



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

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A Littelfuse Technology